IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract as follows:

ABSTRACT

Provided is a A semiconductor integrated circuit device, comprising: is formed by a semiconductor substrate having an SiGe layer and a first Si layer epitaxially grown thereover, and having on which there are element formation regions each partitioned by element isolation regions; a shallow groove isolation, which has a groove formed in each of the element isolation regions and an insulating film inside of the groove, said groove penetrating through the first Si layer and having a bottom in the SiGe layer; a second Si layer formed between the shallow groove isolation and the SiGe layer; and a semiconductor element formed over the main surface of the semiconductor substrate in the element formation regions. The present invention This construction enables a reduction in a-leakage current via the walls of the shallow groove isolation of the strained substrate, thereby improving the element isolation properties.

REMARKS

The specification has been amended to correct errors of a typographical and grammatical nature. Due to the large number of corrections thereto, applicants submit herewith a Substitute Specification, along with a marked-up copy of the original specification for the Examiner's convenience. Applicants submit that the substitute specification includes no new matter. Therefore, entry of the Substitute Specification is respectfully requested.

The abstract has been amended to correct errors of a grammatical nature.

Entry of the preliminary amendments and examination of the application is respectfully requested.

To the extent necessary, applicant's petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 01-2135 (501.42818X00) and please credit any excess fees to such deposit account.

Respectfully submitted,

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